

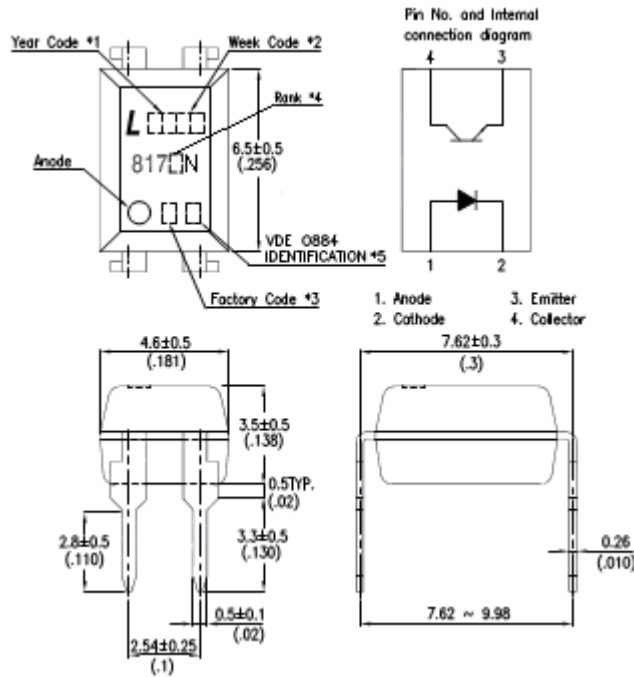


FEATURES

- * Current transfer ratio
(CTR : MIN. 50% at $I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
- * High input-output isolation voltage
($V_{iso} = 5,000\text{Vrms}$)
- * Response time
(t_r : TYP. $4\mu\text{s}$ at $V_{CE} = 2\text{V}$, $I_C = 2\text{mA}$, $R_L = 100\Omega$)
- * Dual-in-line package :
LTV-817-N : 1-channel type
- * Wide lead spacing package :
LTV-817M-N : 1-channel type
- * Surface mounting package :
LTV-817S-N : 1-channel type
- * Tape and reel packaging :
LTV-817S-TA-N, LTV-817S-TA1-N, LTV-817S-TP-N
- * Safety approval
UL , cUL, CSA, FIMKO, NEMKO, DEMKO, SEMKO, VDE, CQC * approved
(*Requires "V" ordering option)
- * RoHS compliance

OUTLINE DIMENSIONS

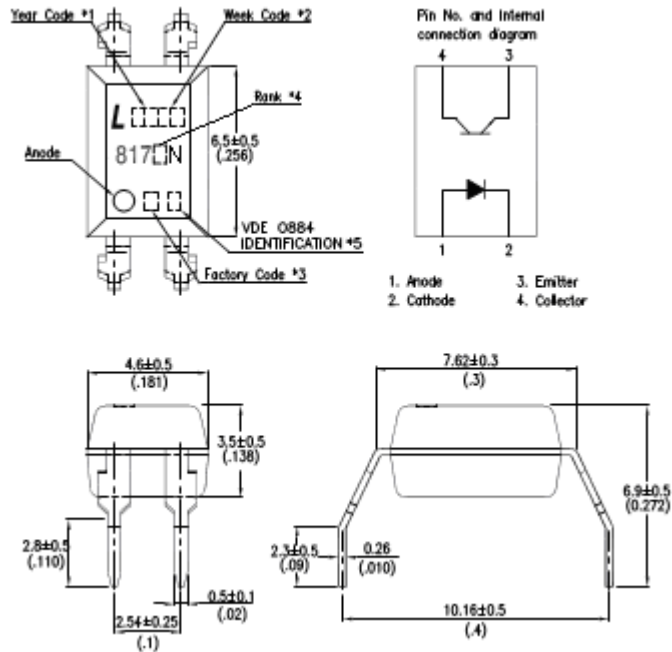
LTV-817-N :



- *1. Year date code.
- *2. 2-digit work week.
- *3. Factory identification mark shall be marked
(W: China-CZ, X : China-TJ, Y : Thailand)
- *4. Rank shall be or shall not be marked.
- *5. "4" or "V" for 4 pin VDE option

OUTLINE DIMENSIONS

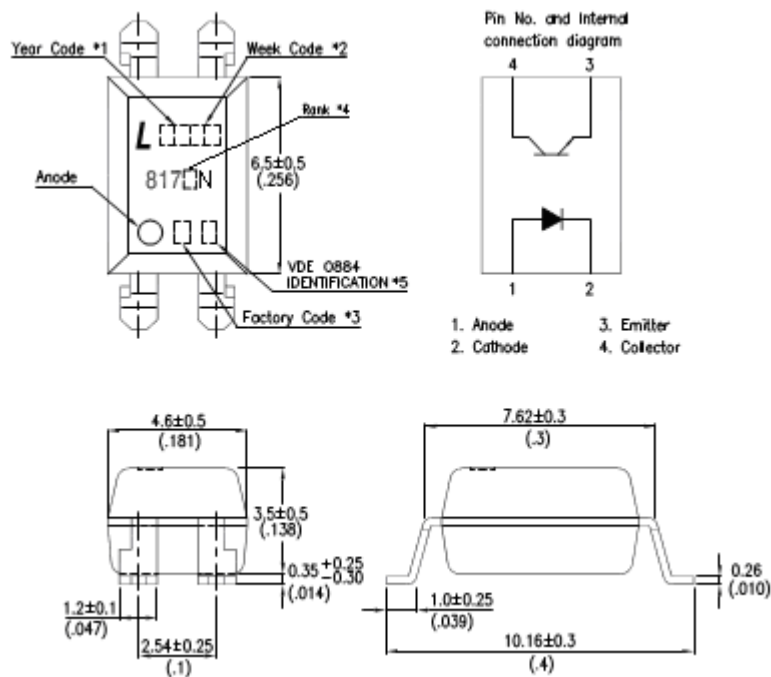
LTV-817M-N :



- *1. Year date code.
- *2. 2-digit work week.
- *3. Factory identification mark shall be marked
(W: China-CZ, X : China-TJ, Y : Thailand)
- *4. Rank shall be or shall not be marked.
- *5. "4" or "V" for 4 pin VDE option

OUTLINE DIMENSIONS

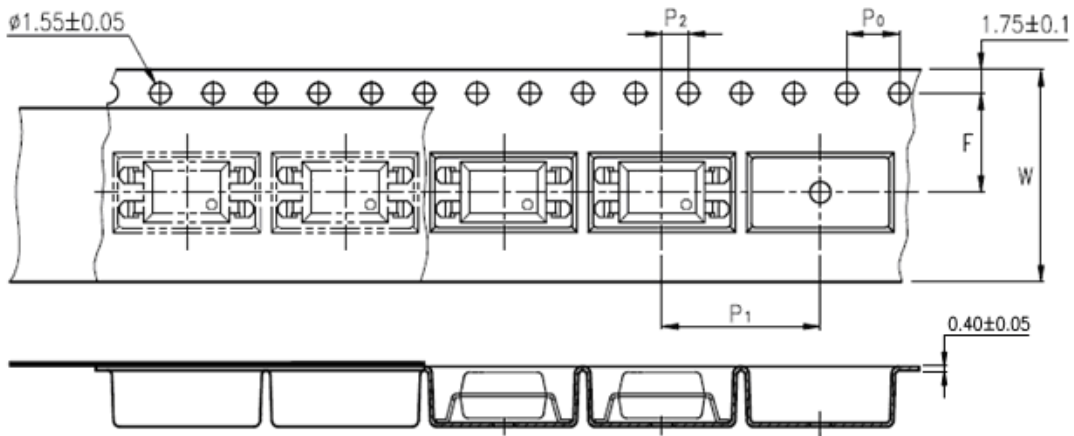
LTV-817S-N :



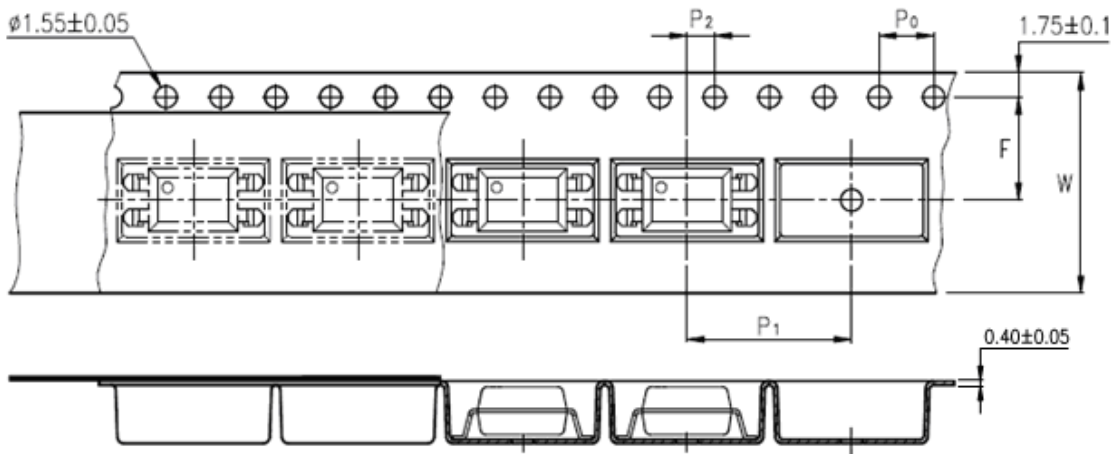
- *1. Year date code.
- *2. 2-digit work week.
- *3. Factory identification mark shall be marked
(W: China-CZ, X : China-TJ, Y : Thailand)
- *4. Rank shall be or shall not be marked.
- *5. "4" or "V" for 4 pin VDE option

TAPING DIMENSIONS

LTV-817S-TA-N :



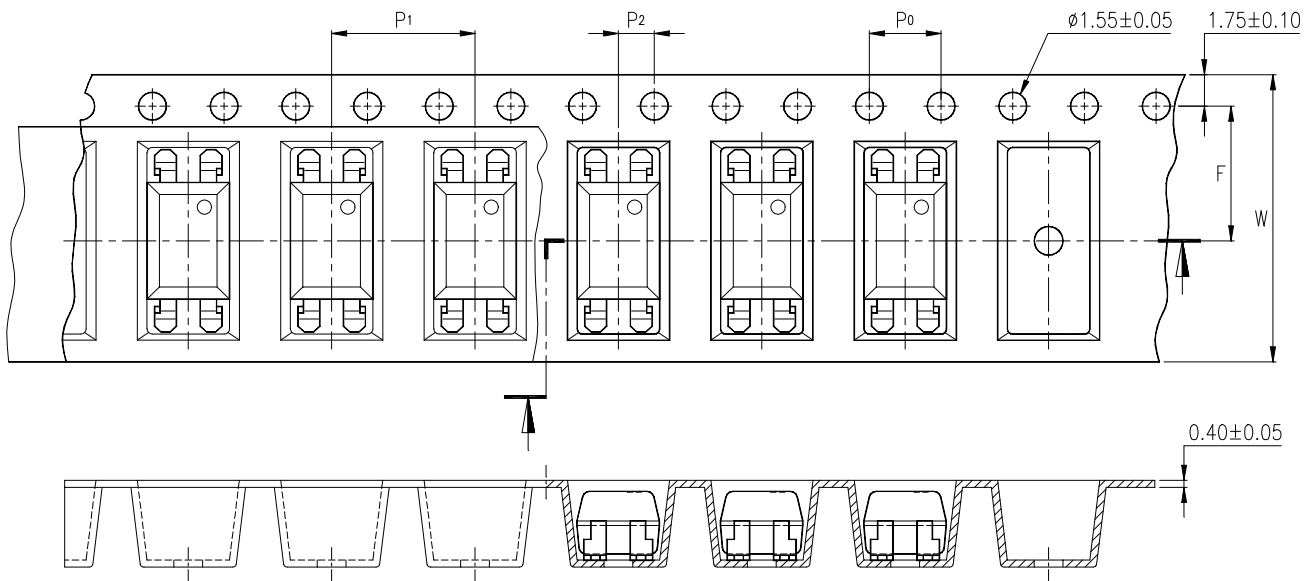
LTV-817S TA1-N :



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	16 ± 0.3 (.63)
Pitch of sprocket holes	P_0	4 ± 0.1 (.15)
Distance of compartment	F	7.5 ± 0.1 (.295)
	P_2	2 ± 0.1 (.079)
Distance of compartment to compartment	P_1	12 ± 0.1 (.472)

TAPING DIMENSIONS

LTV-817S-TP-N :



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	16 ± 0.3 (.630)
Pitch of sprocket holes	P0	4 ± 0.1 (.157)
Distance of compartment	F	7.5 ± 0.1 (.295)
Distance of compartment to compartment	P1	2 ± 0.1 (.079)
Distance of compartment to sprocket hole	P2	8 ± 0.1 (.315)

ABSOLUTE MAXIMUM RATING

(Ta = 25°C)

PARAMETER		SYMBOL	RATING	UNIT
INPUT	Forward Current	I_F	40	mA
	Reverse Voltage	V_R	6	V
	Power Dissipation	P	50	mW
OUTPUT	Collector - Emitter Voltage	V_{CEO}	35	V
	Emitter - Collector Voltage	V_{ECO}	6	V
	Collector Current	I_C	50	mA
	Collector Power Dissipation	P_C	100	mW
Total Power Dissipation		P_{tot}	150	mW
*1	Isolation Voltage	V_{iso}	5,000	Vrms
Operating Temperature		T_{opr}	-30 ~ +110	°C
Storage Temperature		T_{stg}	-55 ~ +125	°C
*2	Soldering Temperature	T_{sol}	260	°C

*1. AC For 1 Minute, R.H. = 40 ~ 60%

Isolation voltage shall be measured using the following method.

- (1) Short between anode and cathode on the primary side and between collector and emitter on the secondary side.
- (2) The isolation voltage tester with zero-cross circuit shall be used.
- (3) The waveform of applied voltage shall be a sine wave.

*2. For 10 Seconds

ELECTRICAL - OPTICAL CHARACTERISTICS

(Ta = 25°C)

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
INPUT	Forward Voltage	V_F	—	1.2	1.4	V	$I_F=20mA$
	Reverse Current	I_R	—	—	10	μA	$V_R=4V$
	Terminal Capacitance	C_t	—	30	250	pF	$V=0, f=1KHz$
OUTPUT	Collector Dark Current	I_{CEO}	—	—	100	nA	$V_{CE}=20V, I_F=0$
	Collector-Emitter Breakdown Voltage	BV_{CEO}	35	—	—	V	$I_C=0.1mA$ $I_F=0$
	Emitter-Collector Breakdown Voltage	BV_{ECO}	6	—	—	V	$I_E=10\mu A$ $I_F=0$
TRANSFER CHARACTERISTICS	Collector Current	I_C	4	—	20	mA	$I_F=5mA$ $V_{CE}=5V$
	* Current Transfer Ratio	CTR	80	—	400	%	
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.2	V	$I_F=20mA$ $I_C=1mA$
	Isolation Resistance	Riso	5×10^{10}	1×10^{11}	—	Ω	DC500V 40 ~ 60% R.H.
	Floating Capacitance	C_f	—	0.6	1	pF	$V=0, f=1MHz$
	Cut-Off Frequency	fc	—	80	—	kHz	$V_{CE}=5V, I_C=2mA$ $R_L=100\Omega, -3dB$
	Response Time (Rise)	t_r	—	4	18	μs	$V_{CE}=2V, I_C=2mA$ $R_L=100\Omega$
	Response Time (Fall)	t_f	—	3	18	μs	

$$* CTR = \frac{I_C}{I_F} \times 100\%$$

RANK TABLE OF CURRENT TRANSFER RATIO CTR

MODEL NO.	RANK MARK	CTR (%)
LTV-817	AN	80 ~ 160
	BN	130 ~ 260
	CN	200 ~ 400

CONDITIONS	$I_F = 5 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $T_a = 25 \text{ }^\circ\text{C}$
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CHARACTERISTICS CURVES

Fig.1 Forward Current vs. Ambient Temperature

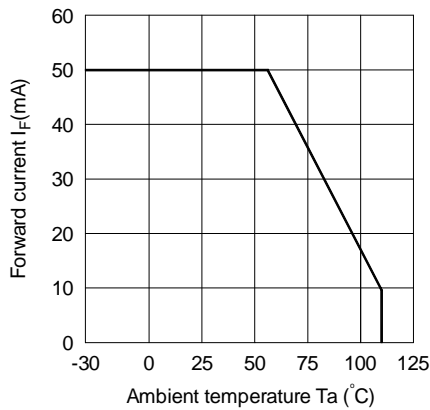


Fig.2 Collector Power Dissipation vs. Ambient Temperature

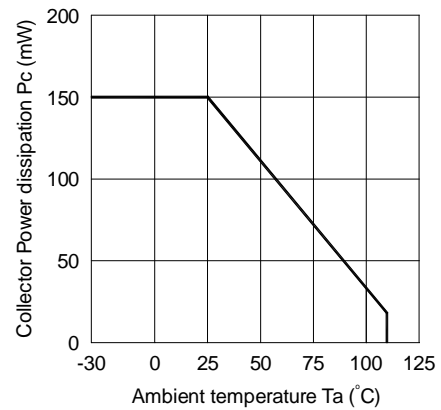


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

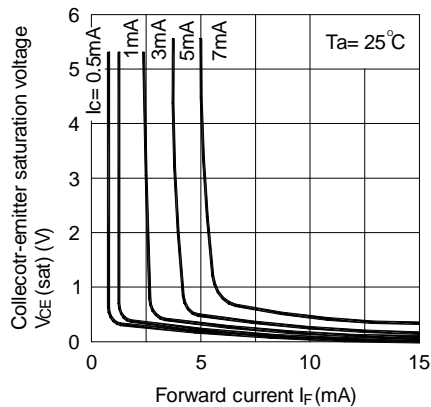


Fig.4 Forward Current vs. Forward Voltage

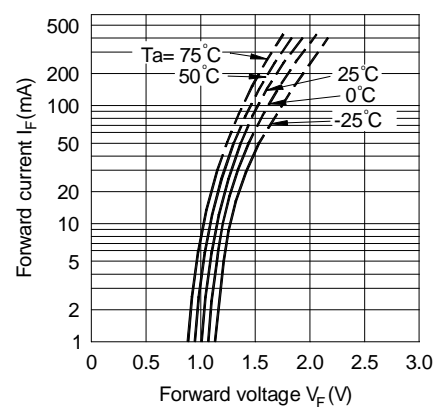


Fig.5 Current Transfer Ratio vs. Forward Current

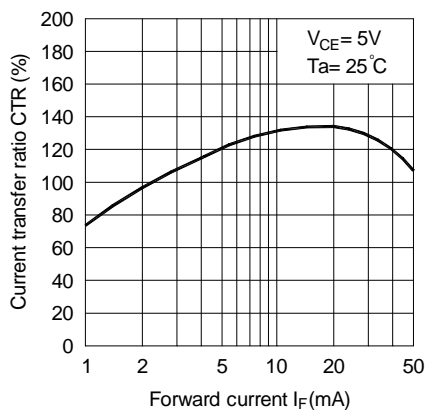
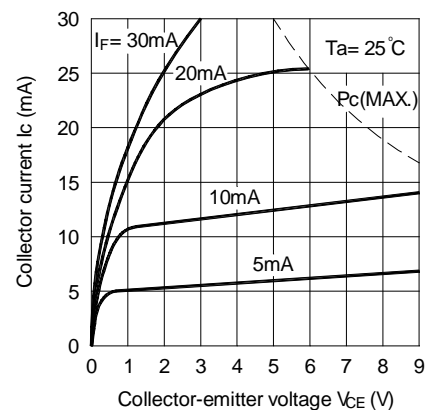


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTICS CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

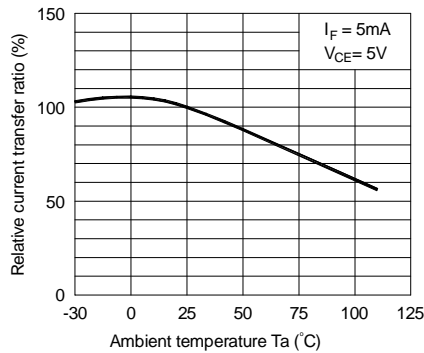


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

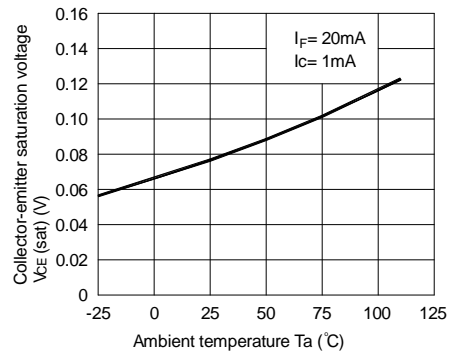


Fig.9 Collector Dark Current vs. Ambient Temperature

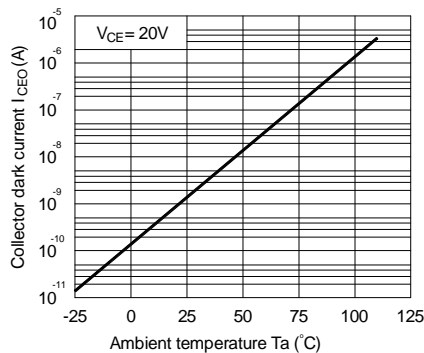


Fig.10 Response Time vs. Load Resistance

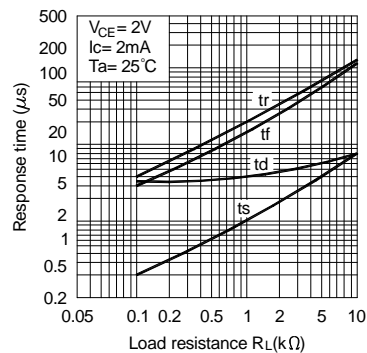
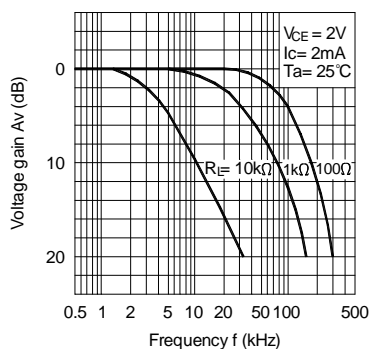
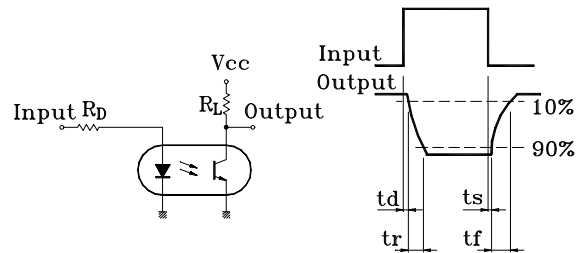


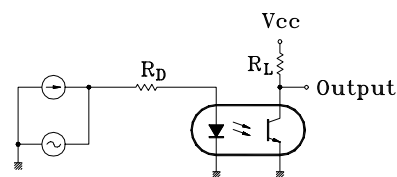
Fig.11 Frequency Response



Test Circuit for Response Time



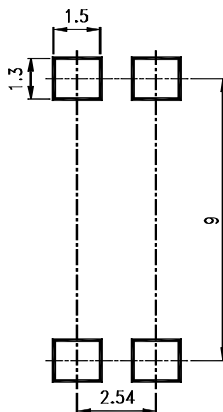
Test Circuit for Frequency Response



RECOMMENDED FOOT PRINT PATTERNS (MOUNT PAD)

Unit : mm

4 PIN



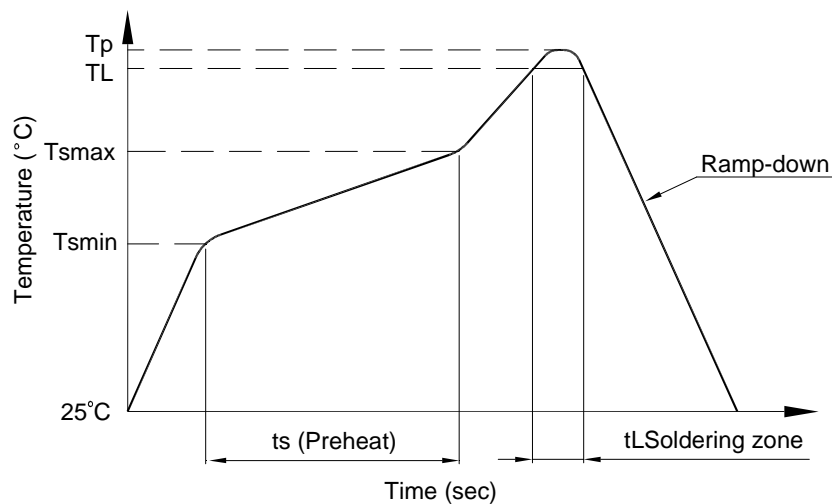
TEMPERATURE PROFILE OF SOLDERING REFLOW

(1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.

1. Wave solder
 - 260°C / 10 sec.

2. IR Reflow

Profile item	Conditions
Preheat	
- Temperature Min (T_{Smin})	150°C
- Temperature Max (T_{Smax})	180°C
- Time (min to max) (ts)	90±30°C
Soldering zone	
- Temperature (T_L)	250°C
- Time (t_L)	10~15 sec
Peak Temperature (T_P)	260°C
Ramp-down rate	3~6°C / sec



(2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.

Keep the temperature on the package of the device within the condition of above (1)

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- Immerse body in solder paste is not recommended.

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